

L Number	Hits	Search Text	DB	Time stamp
-	2	semiconductor and substrate and "SiO.sub.2" and "SiN" and (porous same grain\$1 same (polysilicon or (polycrystalline with silicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/23 13:13
-	154	semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain\$1 same (polysilicon or (polycrystalline with silicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/22 13:34
-	0	semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain\$1 same monolayer same (polysilicon or (polycrystalline with silicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/22 10:42
-	0	semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain\$1 same (monomolecular adj layer) same (polysilicon or (polycrystalline with silicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/22 10:43
-	5	semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain\$1 same (thin adj layer) same (polysilicon or (polycrystalline with silicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/22 10:50
-	0	semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain\$1 same (membrane) same (polysilicon or (polycrystalline with silicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/22 10:50
-	154	semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain\$1 same (polysilicon or (polycrystalline with silicon)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/22 13:34
-	28	(semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain\$1 same (polysilicon or (polycrystalline with silicon)))) and filter	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/22 13:41
-	0	(semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain\$1 same (polysilicon or (polycrystalline with silicon)))) and (sacrificial with layer) and HF	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/22 13:42
-	5	(semiconductor and substrate and "SiO.sub.2" and "SiN" and (grain\$1 same (polysilicon or (polycrystalline with silicon)))) and (sacrificial with layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/22 15:45
-	0	semiconductor and (micromachined with encapsulation) and (permeable with polysilicon) and HF	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/22 15:46
-	0	semiconductor and (micromachined with encapsulation) and (polysilicon) and HF	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/22 15:46
-	183	semiconductor and (micromachined) and (polysilicon) and HF	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/22 15:47
-	0	(semiconductor and (micromachined) and (polysilicon) and HF) and SiO and SiN	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/01/22 15:47

-	24	(semiconductor and (micromachined) and (polysilicon) and HF) and SiN	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 15:47
-	22	((semiconductor and (micromachined) and (polysilicon) and HF) and SiN) and oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 15:56
-	19	Lebouitz.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 15:56
-	8	Lebouitz.in. and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 15:57
-	8	(Lebouitz.in. and polysilicon) and oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 15:57
-	8	((Lebouitz.in. and polysilicon) and oxide) and nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/22 15:57
-	10	"718010"	USPAT; US-PGPUB	2003/01/23 13:14